

ABSTRACT OF THE DISCLOSURE

A memory cell has a first switching element, a second switching element and a storage capacitor and formed in an active region. A first bit line and a first word line are connected to the first switching element and a second bit line and a second word line are connected to the second switching element. A plurality of the memory cells are formed within the active region which extends in a straight line. The active region extends at an angle with respect to the bit and word lines. The active region thus has no bent portions. The deterioration of the characteristics of the memory cell caused by the bent portions can be prevented.